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FDZ371PZ

P-Channel 1.5 V Specified PowerTrench[®] Thin WL-CSP MOSFET -20 V, -3.7 A, 75 mΩ

Features

- Max $r_{DS(on)}$ = 75 mΩ at $V_{GS} = -4.5$ V, $I_D = -2.0$ A
- Max $r_{DS(on)}$ = 90 mΩ at $V_{GS} = -2.5$ V, $I_D = -1.5$ A
- Max $r_{DS(on)}$ = 110 mΩ at $V_{GS} = -1.8$ V, $I_D = -1.0$ A
- Max $r_{DS(on)}$ = 150 mΩ at $V_{GS} = -1.5$ V, $I_D = -1.0$ A
- Occupies only 1.0 mm² of PCB area. Less than 30% of the area of 2 x 2 BGA
- Ultra-thin package: less than 0.4 mm height when mounted to PCB
- HBM ESD protection level >4.4kV typical (Note 3)
- RoHS Compliant

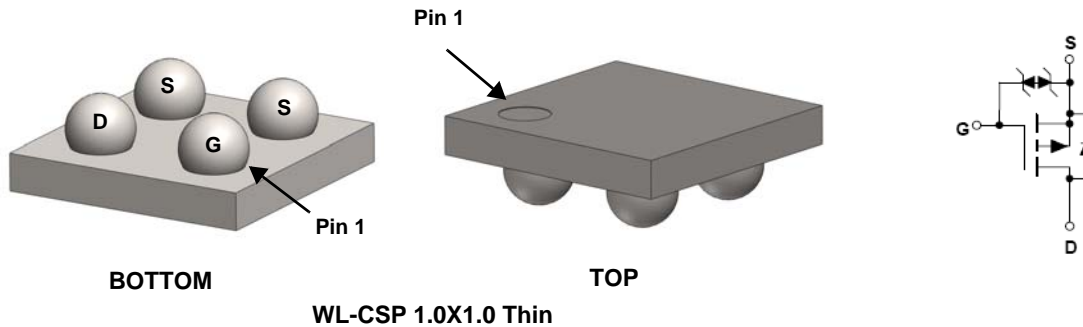


General Description

Designed on Fairchild's advanced 1.5 V PowerTrench[®] process with state of the art "fine pitch" Thin WLCSP packaging process, the FDZ371PZ minimizes both PCB space and $r_{DS(on)}$. This advanced WLCSP MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, ultra-low profile packaging, low gate charge, and low $r_{DS(on)}$.

Applications

- Battery management
- Load switch
- Battery protection



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	±8	V
I_D	-Continuous	$T_A = 25^\circ\text{C}$ (Note 1a)	-3.7
	-Pulsed		-12
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1a)	1.7
	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1b)	0.5
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Rated	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	75
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	260

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
K	FDZ371PZ	WL-CSP 1.0X1.0 Thin	7"	8 mm	5000 units

FDZ371PZ P-Channel 1.5 V Specified PowerTrench[®] Thin WL-CSP MOSFET

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = -250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		22		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}$, $V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{ V}$, $V_{DS} = 0\text{ V}$			± 10	μA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250\text{ }\mu\text{A}$	-0.35	-0.6	-1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		-4		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = -4.5\text{ V}$, $I_D = -2.0\text{ A}$		55	75	m Ω
		$V_{GS} = -2.5\text{ V}$, $I_D = -1.5\text{ A}$		65	90	
		$V_{GS} = -1.8\text{ V}$, $I_D = -1.0\text{ A}$		80	110	
		$V_{GS} = -1.5\text{ V}$, $I_D = -1.0\text{ A}$		100	150	
		$V_{GS} = -4.5\text{ V}$, $I_D = -2.0\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$		80	124	
g_{FS}	Forward Transconductance	$V_{DD} = -5\text{ V}$, $I_D = -3.3\text{ A}$		14		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		750	1000	pF
C_{oss}	Output Capacitance			110	145	pF
C_{rss}	Reverse Transfer Capacitance			100	150	pF

Switching Characteristics

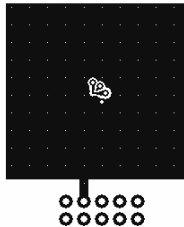
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -10\text{ V}$, $I_D = -3.3\text{ A}$, $V_{GS} = -4.5\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		5.9	12	ns
t_r	Rise Time			9.1	18	ns
$t_{d(off)}$	Turn-Off Delay Time			124	198	ns
t_f	Fall Time			88	140	ns
Q_g	Total Gate Charge			12	17	nC
Q_{gs}	Gate to Source Charge	$V_{GS} = -4.5\text{ V}$, $V_{DD} = -10\text{ V}$, $I_D = -3.3\text{ A}$		1.1		nC
Q_{gd}	Gate to Drain "Miller" Charge			3.4		nC

Drain-Source Diode Characteristics

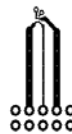
I_S	Maximum Continuous Drain-Source Diode Forward Current				-1.1	A
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = -1.3\text{ A}$ (Note 2)		-0.7	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F = -3.3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		61	98	ns
Q_{rr}	Reverse Recovery Charge			29	47	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{ in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $75\text{ }^\circ\text{C/W}$ when mounted on a 1 in^2 pad of 2 oz copper.



b. $260\text{ }^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < $300\mu\text{s}$, Duty cycle < 2.0%.

3. The diode connected between the gate and source serves only as protection ESD. No gate overvoltage rating is implied.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

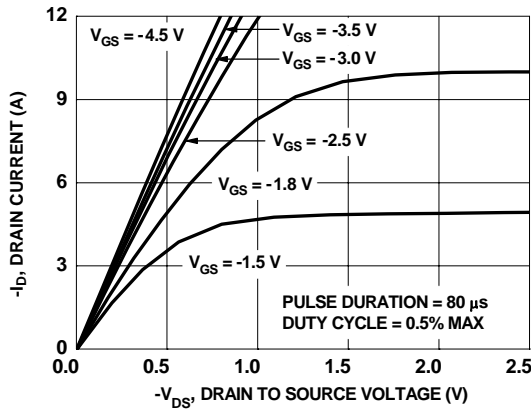


Figure 1. On-Region Characteristics

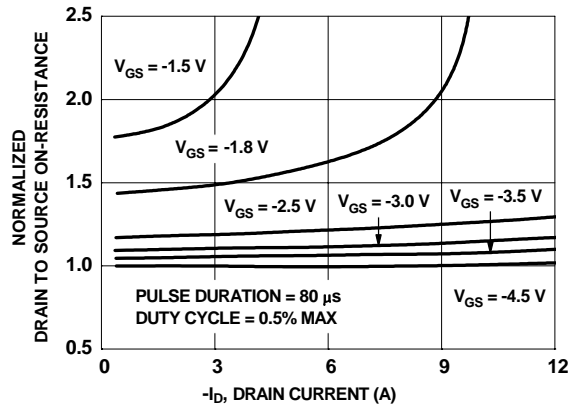


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

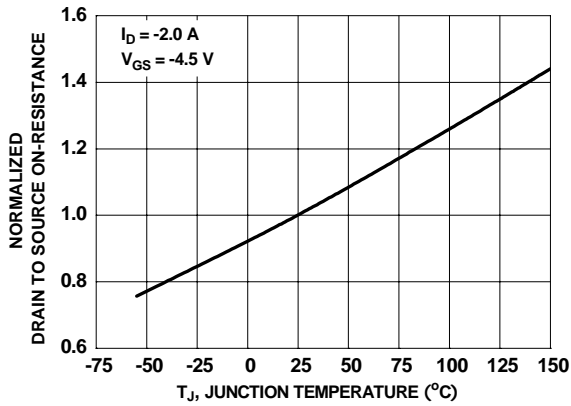


Figure 3. Normalized On-Resistance vs Junction Temperature

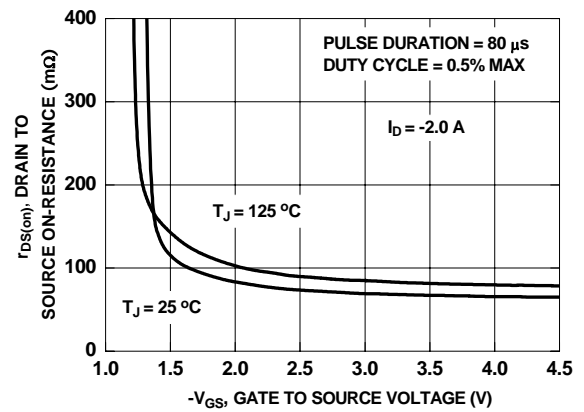


Figure 4. On-Resistance vs Gate to Source Voltage

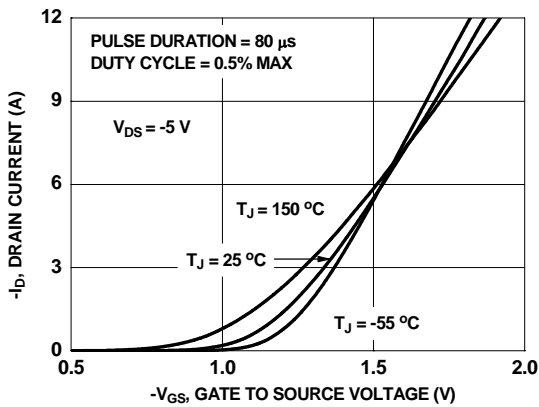


Figure 5. Transfer Characteristics

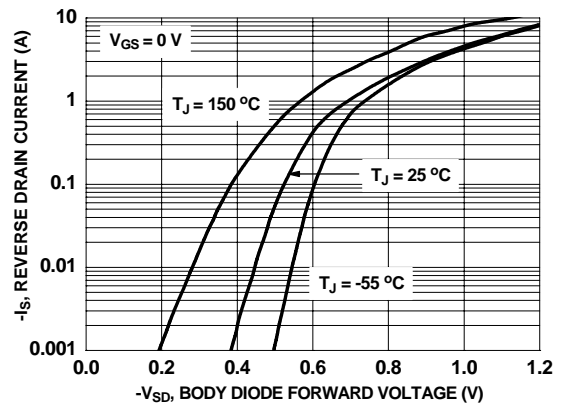


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

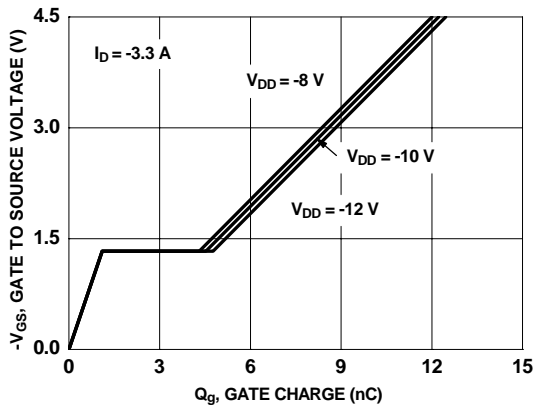


Figure 7. Gate Charge Characteristics

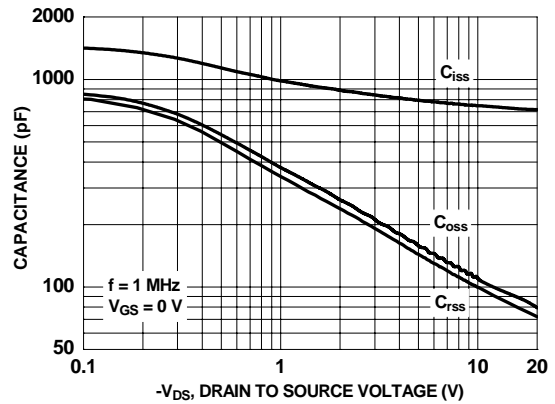


Figure 8. Capacitance vs Drain to Source Voltage

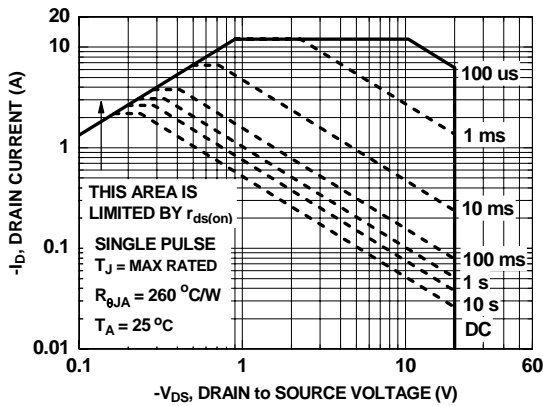


Figure 9. Forward Bias Safe Operating Area

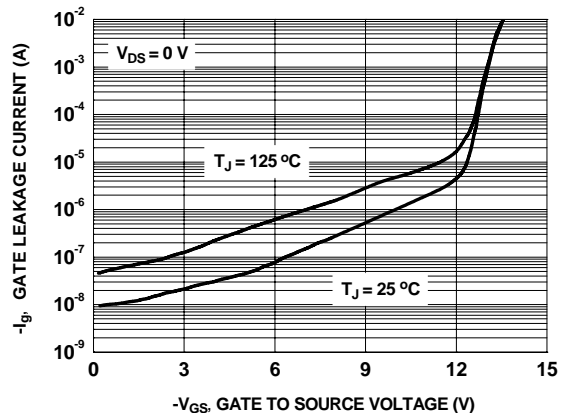


Figure 10. Gate Leakage Current vs Gate to Source Voltage

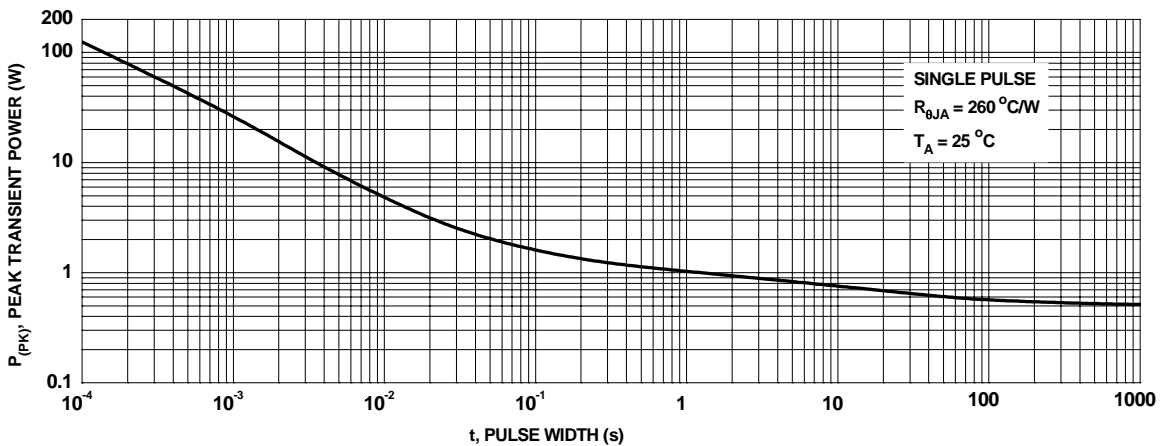


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

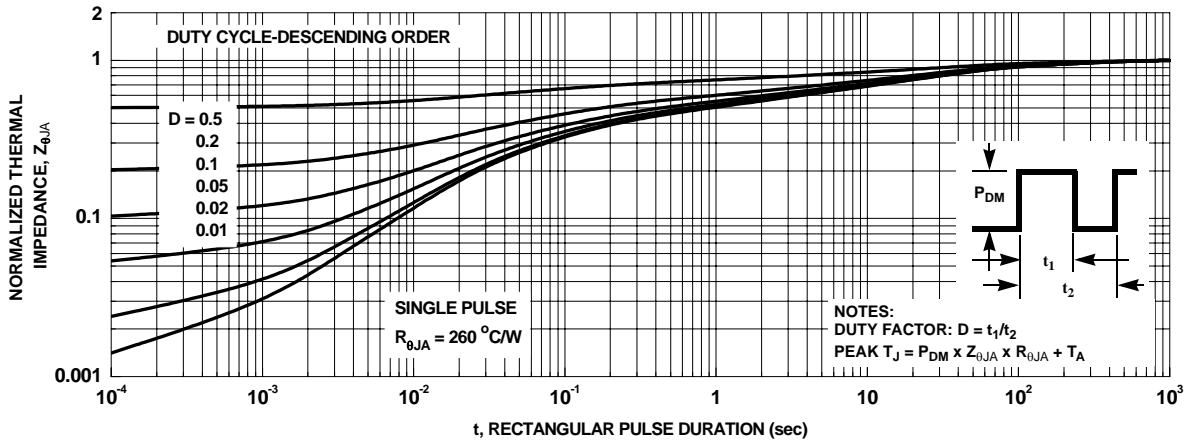
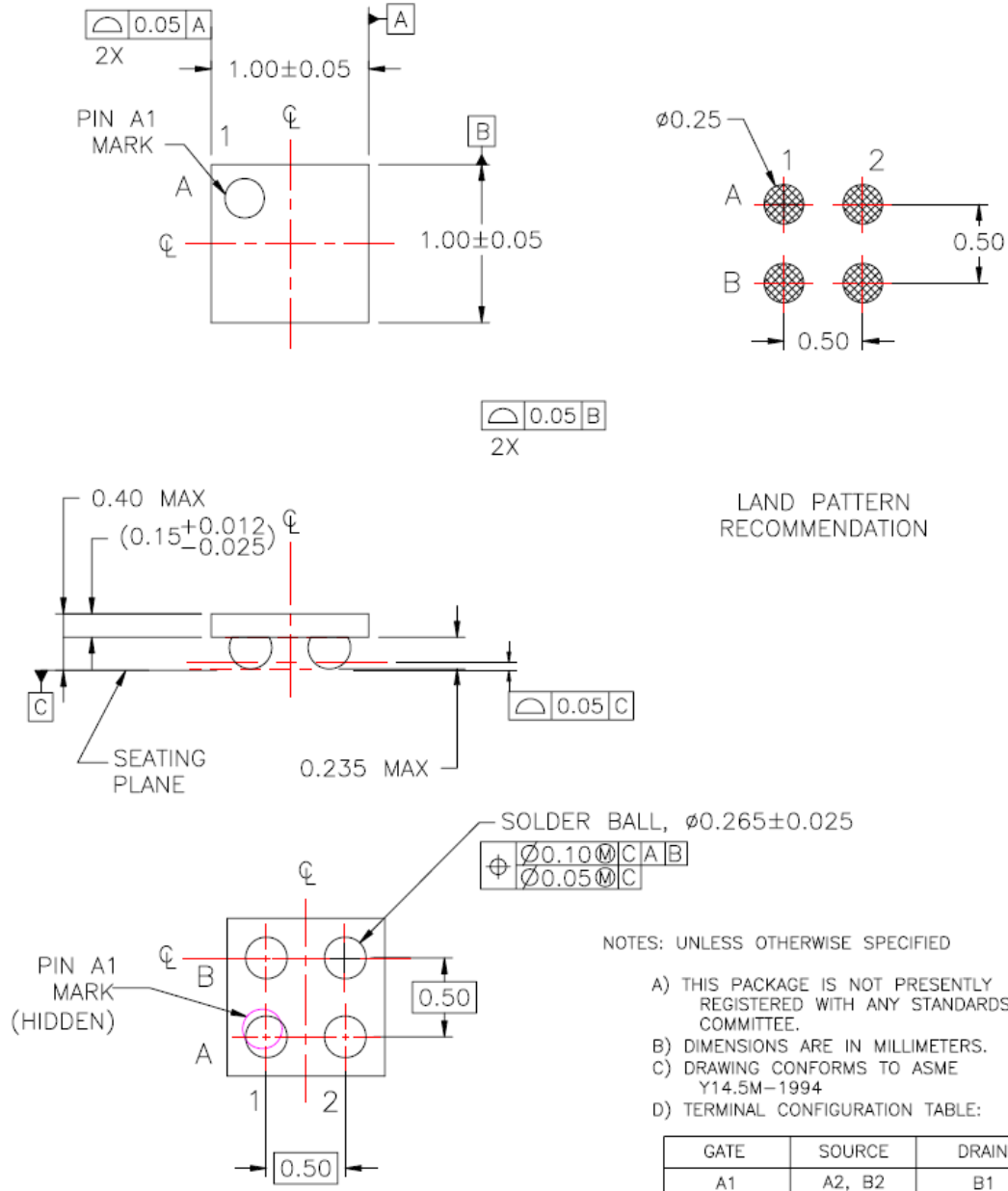


Figure 12. Junction-to-Ambient Transient Thermal Response Curve

Dimensional Outline and Pad Layout



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE IS NOT PRESENTLY REGISTERED WITH ANY STANDARDS COMMITTEE.
 - B) DIMENSIONS ARE IN MILLIMETERS.
 - C) DRAWING CONFORMS TO ASME Y14.5M-1994
 - D) TERMINAL CONFIGURATION TABLE:
- | GATE | SOURCE | DRAIN |
|------|--------|-------|
| A1 | A2, B2 | B1 |
- E) DRAWING FILENAME: MKT-UC004ADREV2

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http://www.fairchildsemi.com/package/packageDetails.html?id=PN_UCBAA-004

